

L Number	Hits	Search Text	DB	Time stamp
1	1182	((passiv\$8 near (layer or region or film or medium)) and semiconductor and monolithic and integrated and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:02
8	1	((passiv\$8 near (layer or region or film or medium)) and semiconductor and monolithic and integrated and substrate) and VCSEL and ((active near (layer or device or film or region or medium)) with amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 08:59
15	3	((passiv\$8 near (layer or region or film or medium)) and semiconductor and monolithic and integrated and substrate) and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:02
22	6	((passiv\$8 near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:13
29	1	((passiv\$8 near (layer or region or film or medium)) and semiconductor and 372/50 and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:04
36	1	((passiv\$8 near (layer or region or film or medium)) and semiconductor and 372/\$ and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:11
43	9	((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and 372/\$ and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:13
50	17	((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:41
57	17	((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:41
71	14	((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and (diode near laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:42
64	17	((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:17
78	11	((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:22

85	6	(((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) not (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:27
92	2	mesa and (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:27
99	11	amplif\$5 and (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:27
106	0	(((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium)))) not (amplif\$5 and (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:28
113	11	(((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium)))) AND t (amplif\$5 and (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEL and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:28
127	24698	(substrate near\$3 (GaAs or AsGa))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:28
134	1390	(substrate near\$3 (GaN or NGa))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:28
141	17941	(substrate near\$3 (InP or PIn))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:28

148	78	((substrate near\$ (GaAs or AsGa))) and ((substrate near\$ (GaN or NGa))) and ((substrate near\$ (InP or PIn)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:29
162	0	"11" and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:29
169	0	("11" and photodiode) and (photodiode or photodetect\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:30
155	11	((substrate near\$ (GaAs or AsGa))) and ((substrate near\$ (GaN or NGa))) and ((substrate near\$ (InP or PIn))) and VCSEL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:30